MICROWAVE POWER GaAs FET

Internally Matched Power GaAs FETs (X, Ku-Band)

Features

- High power
 - $P_{1dB} = 37.5 \text{ dBm}$ at 14.0 GHz to 14.5 GHz
- High gain
 - $G_{1dB} = 6.0 \text{ dB}$ at 14.0 GHz to 14.5 GHz
- Broad Band Internally Matched
- Hermetically sealed package

RF Performance Specifications (T_a = 25° C)

Characteristics	Symbol	ymbol Condition		Min.	Тур.	Max
Output Power at 1dB Compression Point	P _{1dB}		dBm	37.0	37.5	_
Power Gain at 1dB Compression Point	G _{1dB}	V _{DS} = 9V f = 14.0 ~ 14.5GHz	dB	5.0	6.0	_
Drain Current	I _{DS}		Α	1	2.0	2.5
Power Added Efficiency	η_{add}		%	_	20	_
Channel-Temperature Rise	ΔT_{ch}	V _{DS} X I _{DS} X R _{th(c-c)}	°C	-	_	80

Electrical Characteristics (T_a = 25° C)

Characteristic	Symbol	Condition	Unit	Min.	Тур.	Max
Trans-conductance	gm	V _{DS} =3V I _{DS} =2.4 A	mS	_	1400	_
Pinch-off Voltage	V_{GSoff}	V_{DS} =3V I_{DS} =72mA	V	-2.0	-3.5	-5.0
Saturated Drain Current	I _{DSS}	V _{DS} =3V V _{GS} =0V	Α	_	5.0	5.7
Gate to Source Breakdown Voltage	$V_{\rm GSO}$	I _{GS} =72 μA	V	-5	-	_
Thermal Resistance	R _{th (c-c)}	Channel to case	°C/W	_	3.0	3.7

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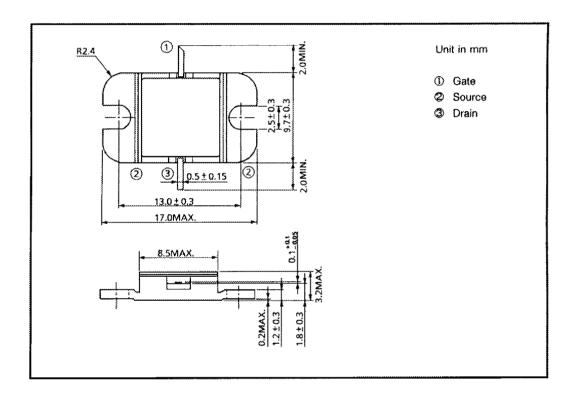
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Absolute Maximum Ratings ($T_a = 25^{\circ} C$)

Characteristic	Symbol	Unit	Rating
Drain Source Voltage	V_{DS}	V	15
Gate Source Voltage	V _{GS}	V	-5
Drain Current	I _{DS}	Α	5.7
Total Power Dissipation (Tc = 25°C)	P_{T}	W	30
Channel Temperature	T _{ch}	°C	175
Storage Temperature	T _{stg}	,C	-65~175

Package Outline (2-9D1B)

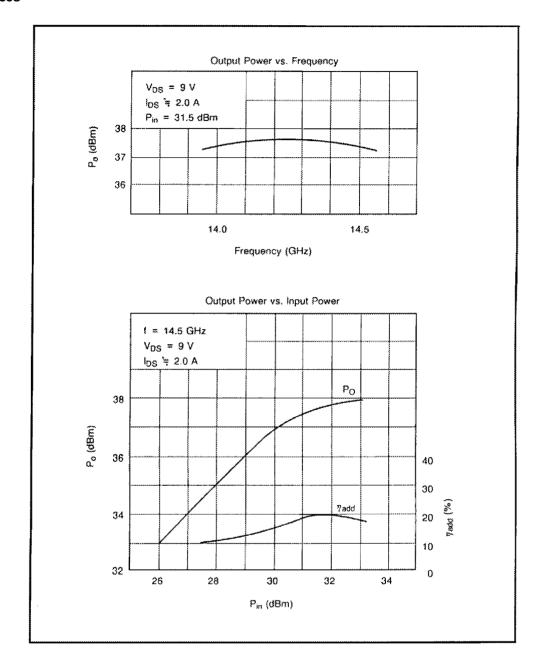


Handling Precautions for Packaged Type

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

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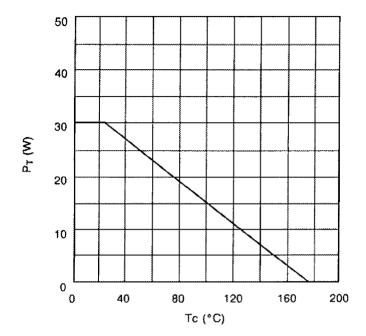
RF Performances



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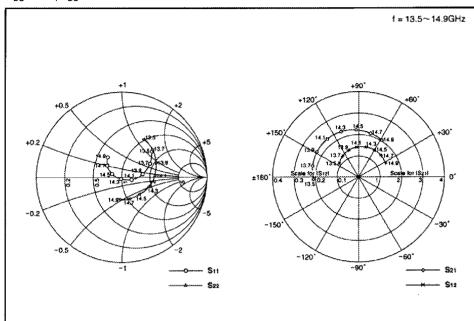
Power Dissipation vs. Case Temperature



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Tim1414-5 S-Parameters (MAGN. and ANGLES)

 V_{DS} = 9 V, I_{DS} = 2 A



FREQUENCY (GHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
13.50	0.47	41	2.10	-177	0.111	144	0.52	60
13.60	0.42	34	2.16	175	0.118	136	0.51	51
13.70	0.37	26	2.20	166	0.124	127	0.49	42
13.80	0.31	18	2.25	157	0.130	119	0.47	33
13.90	0.25	9	2.28	148	0.135	110	0.44	23
14.00	0.19	~1	2.30	139	0.139	102	0.42	13
14.10	0.12	-13	2.31	129	0.142	94	0.39	3
14.20	0.06	-32	2.30	120	0.145	85	0.36	-8
14.30	0.02	-113	2.29	111	0.146	76	0.34	-19
14.40	0.07	178	2.26	102	0.148	68	0.31	-31
14.50	0.12	160	2.22	93	0.147	60	0.29	-43
14.60	0.17	149	2.18	84	0.147	51	0.28	-56
14.70	0.22	140	2.13	75	0.146	44	0.27	-68
14.80	0.26	132	2.09	66	0.144	36	0.27	-81
14.90	0.29	124	2.04	58	0.142	28	0.29	-93